



WBFBP-03D Plastic-Encapsulate Diodes

DK4448LLD03 SWITCHING DIODE

DESCRIPTION

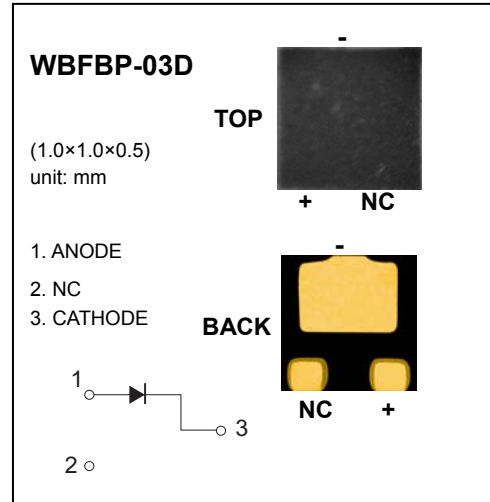
Epitaxial planar silicon diode

FEATURES

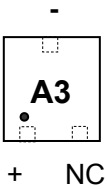
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance
- Lead Free Product

APPLICATION

High Conductance Ultra Fast Diode
 For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM,
 DVD-ROM, Note book PC, etc.)



MARKING: A3



Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	80	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	57	V
Forward Continuous Current	I_{FM}	500	mA
Average Rectified Output Current	I_O	250	mA
Peak Forward Surge Current @t=1.0μs @t=1.0s	I_{FSM}	4.0 2.0	A
Power Dissipation	P_D	100	mW
Thermal Resistance Junction to Ambient	$R_{θJA}$	1250	°C/W
Storage Temperature	T_{STG}	-55 ~ +150	°C

Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V_R	80			V	$I_R=2.5\mu A$
Forward voltage	V_{F1}	0.62		0.72	V	$I_F=5mA$
	V_{F2}			0.855	V	$I_F=10mA$
	V_{F3}			1.0	V	$I_F=100mA$
	V_{F4}			1.25	V	$I_F=150mA$
Reverse current	I_{R1}			0.1	μA	$V_R=70V$
	I_{R2}			25	nA	$V_R=20V$
Capacitance between terminals	C_T			3.5	pF	$V_R=6V, f=1MHz$
Reverse recovery time	t_{rr}			4	ns	$V_R=6V, I_F=5mA$